



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

CPH5520 — PNP/NPN Epitaxial Planar Silicon Transistors

High-Current Switching Applications

Applications

- Relay drivers, lamp drivers, motor drivers, gate drivers

Features

- Composite type with a PNP transistor and an NPN transistor contained in one package, facilitating high-density mounting
- Ultrasmall package facilitate miniaturization in end products. (0.9mm mounting height)

Specifications () : PNP

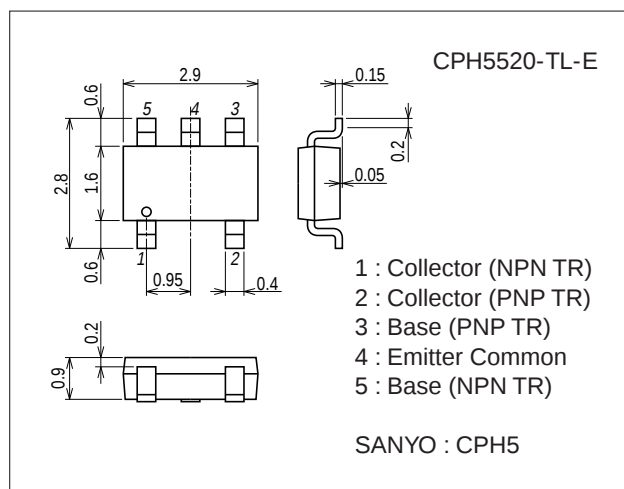
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		(-50)80	V
Collector-to-Emitter Voltage	V _{CEO}		(-50)50	V
Emitter-to-Base Voltage	V _{EBO}		(-)6	V
Collector Current	I _C		(-)2	A
Collector Current (Pulse)	I _{CP}		(-)5	A
Base Current	I _B		(-)400	mA
Collector Dissipation	P _C	Mounted on a ceramic board (600mm ² ×0.8mm) 1unit	0.9	W
Total Power Dissipation	P _T	Mounted on a ceramic board (600mm ² ×0.8mm)	1.2	W
Junction Temperature	T _j		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Package Dimensions

unit : mm (typ)

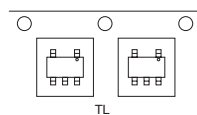
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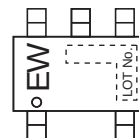
Product & Package Information

- Package : CPH5
- JEITA, JEDEC : SC-74A, SOT-25
- Minimum Packing Quantity : 3,000 pcs./reel

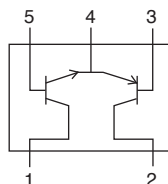
Packing Type : TL



Marking



Electrical Connection

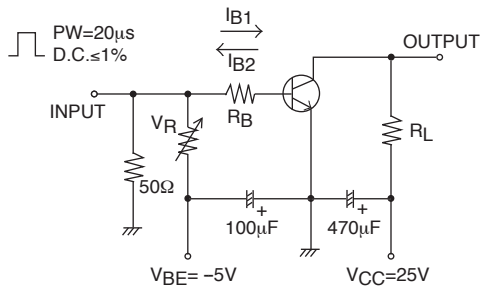


CPH5520

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)40V, I_E=0A$			(-) 1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)4V, I_C=0A$			(-) 1	μA
DC Current Gain	h_{FE}	$V_{CE}=(-)2V, I_C=(-)100mA$	200		560	
Gain-Bandwidth Product	f_T	$V_{CE}=(-)10V, I_C=(-)300mA$		420		MHz
Output Capacitance	C_{ob}	$V_{CB}=(-)10V, f=1MHz$		(16) 8		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)1A, I_B=(-)50mA$		(-165) 130	(-330) 260	mV
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)1A, I_B=(-)50mA$		(-) 0.9	(-) 1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0A$	(-50) 80			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1mA, R_{BE}=\infty$	(-50) 50			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu A, I_C=0A$	(-) 6			V
Turn-On Time	t_{on}	See specified Test Circuit.		(35) 35		ns
Storage Time	t_{stg}			(200) 330		ns
Fall Time	t_f			(24) 40		ns

Switching Time Test Circuit

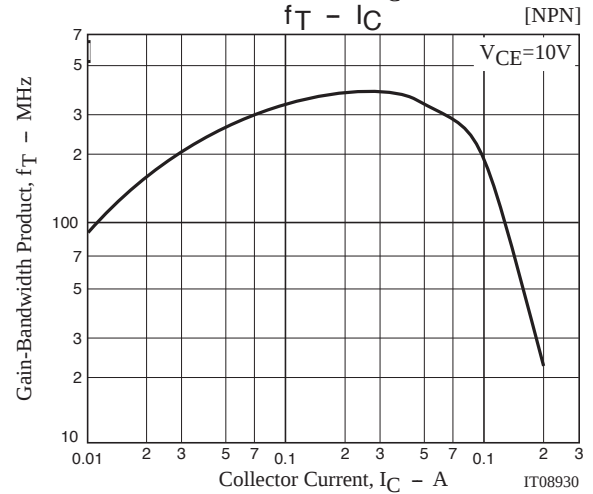
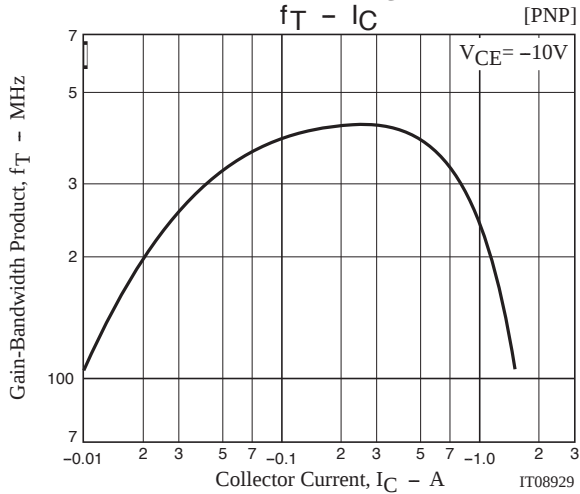
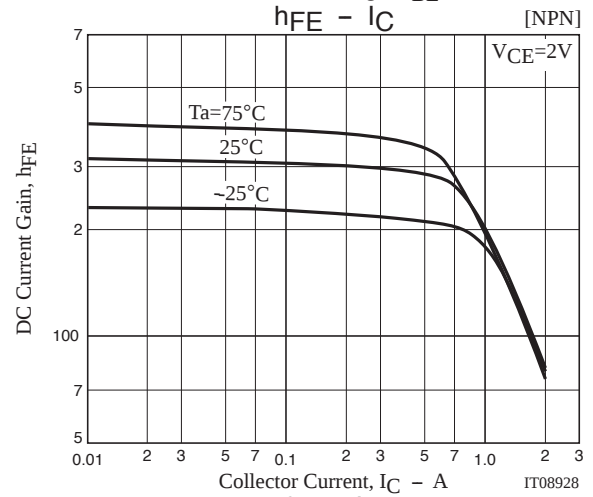
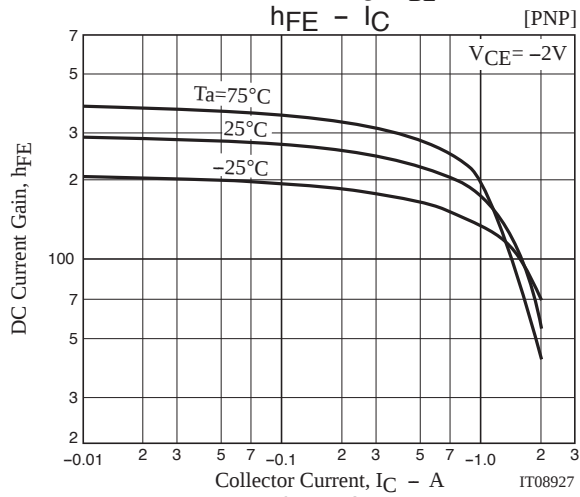
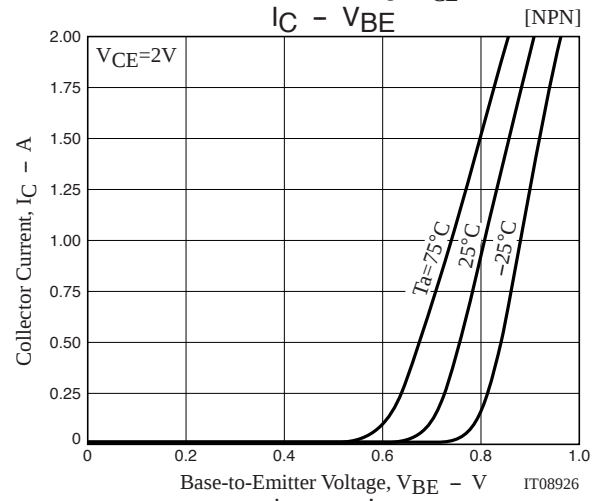
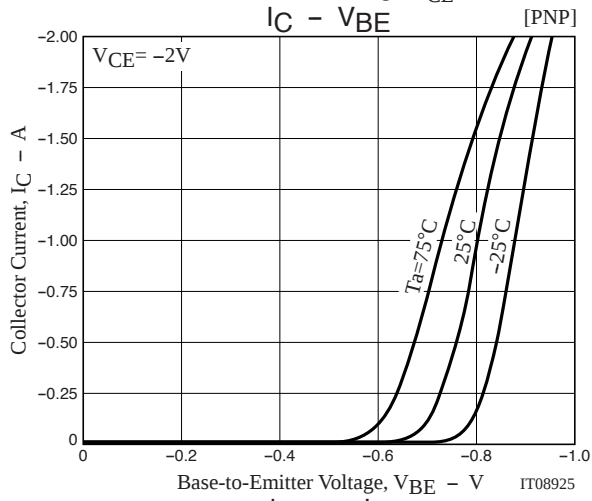
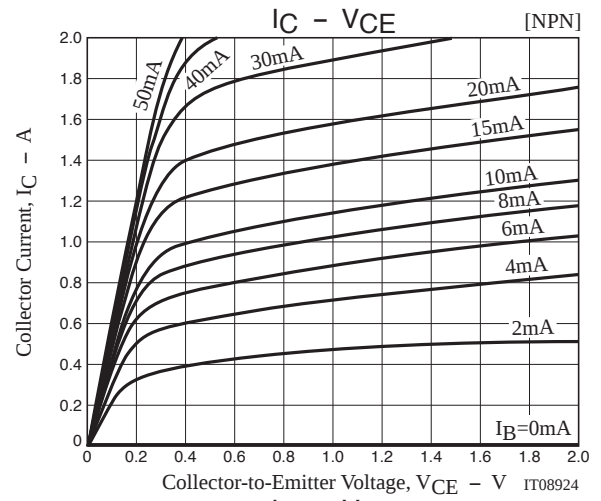
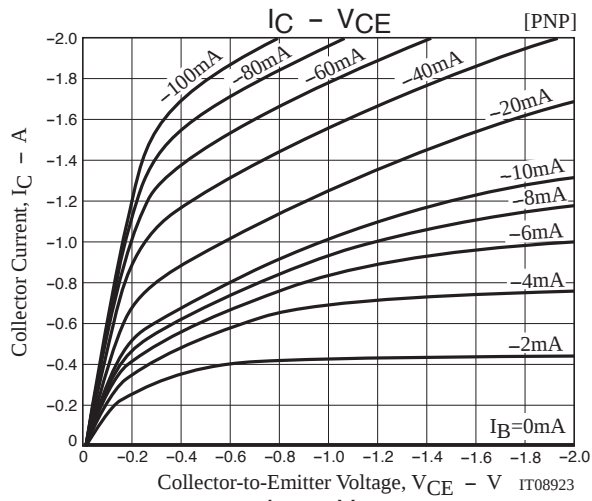


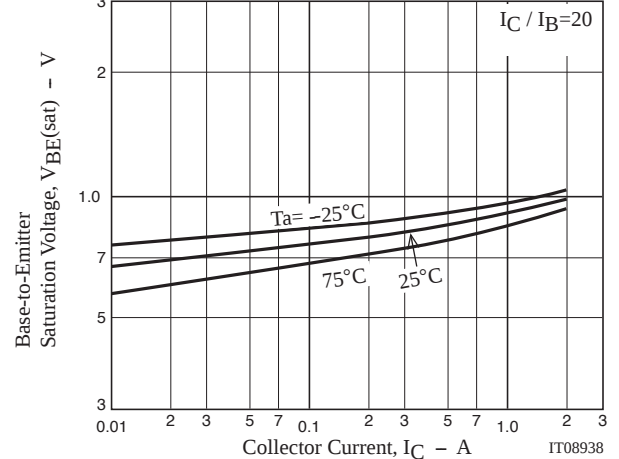
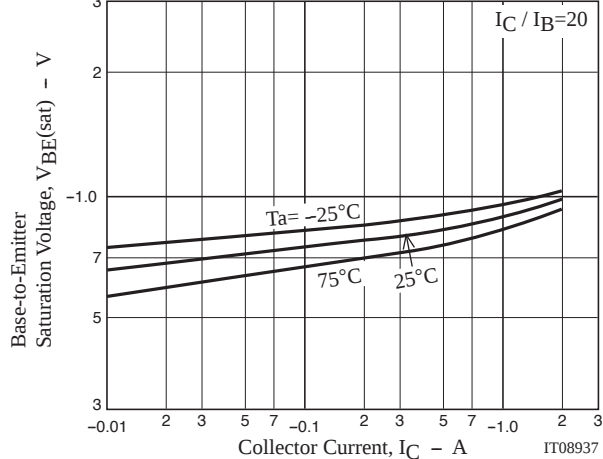
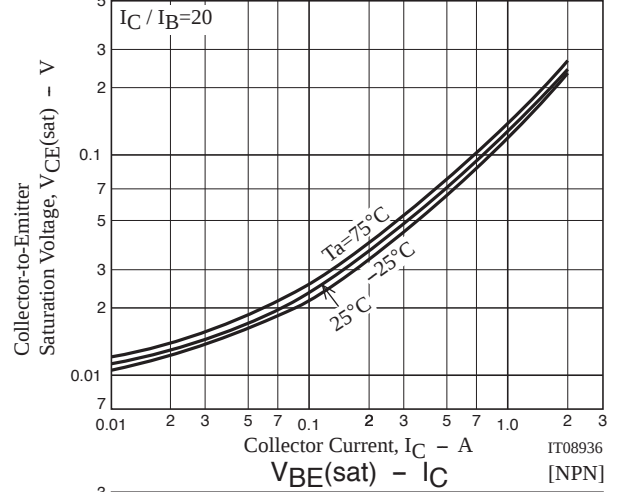
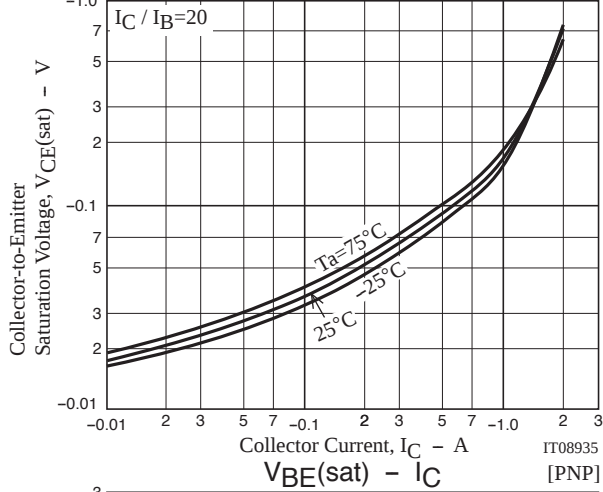
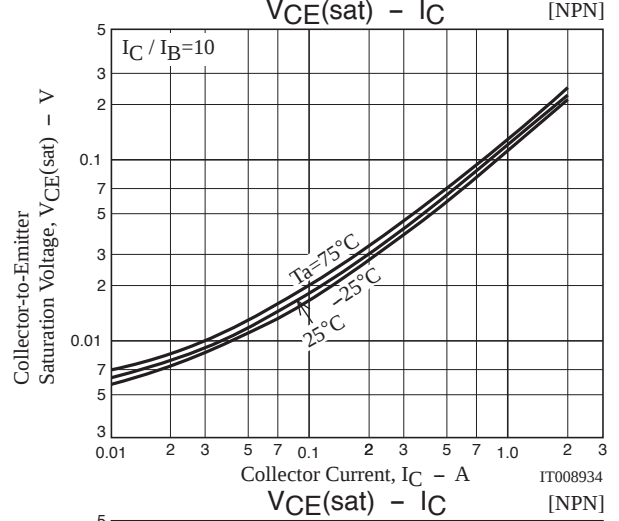
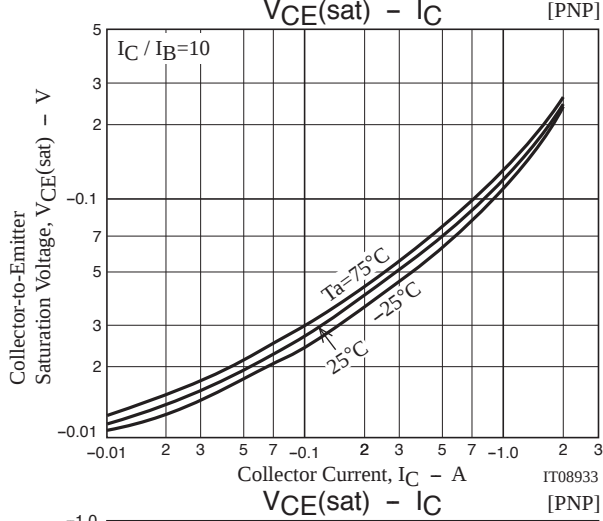
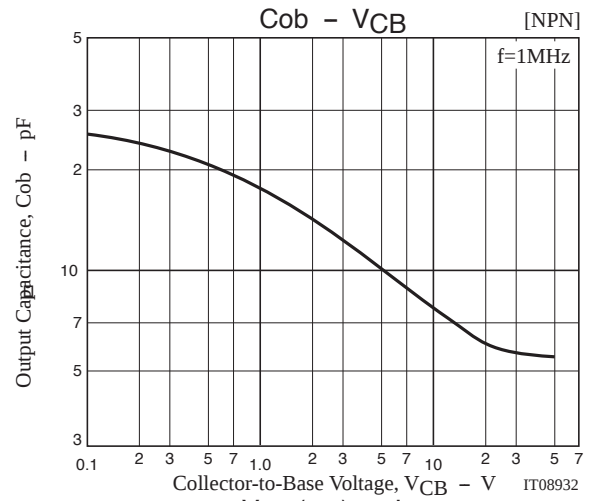
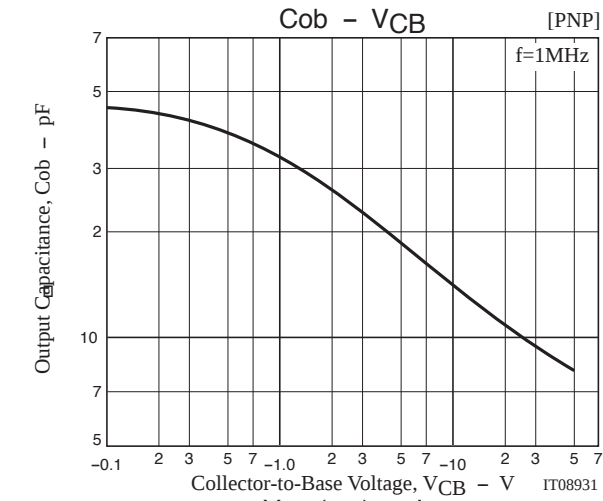
$$I_C = 10I_{B1} = -10I_{B2} = 0.7A$$

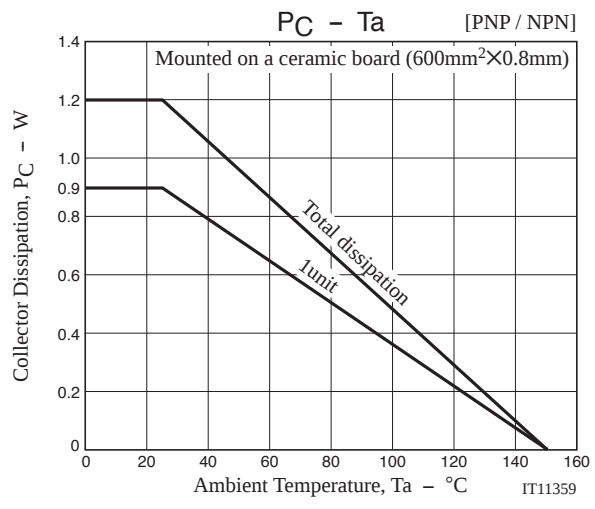
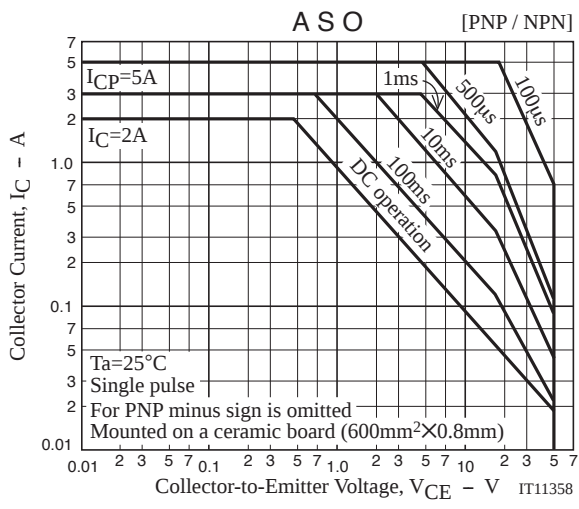
For PNP, the polarity is reversed.

Ordering Information

Device	Package	Shipping	memo
CPH5520-TL-E	CPH5	3,000pcs./reel	Pb Free







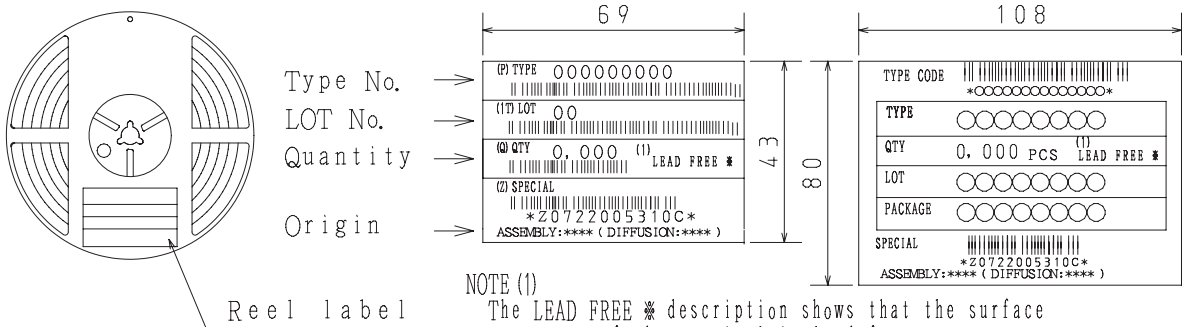
Embossed Taping Specification

CPH5520-TL-E

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
CPH5	CPH6	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

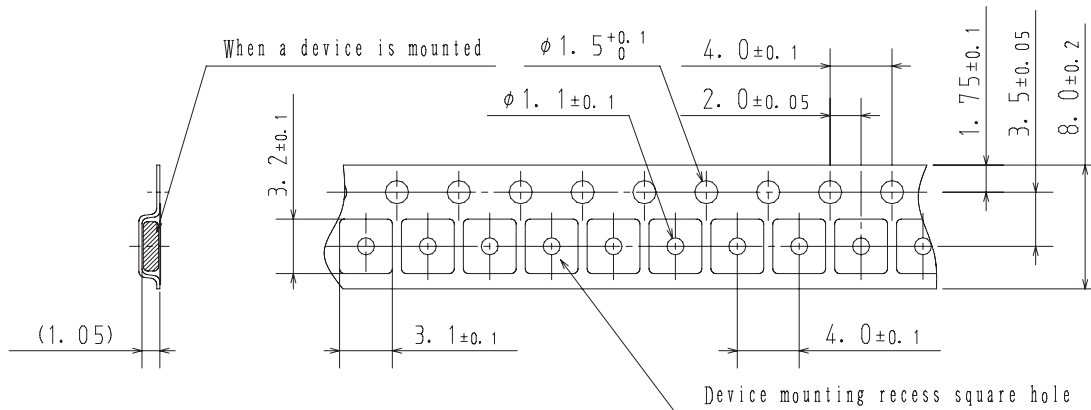
Packing method



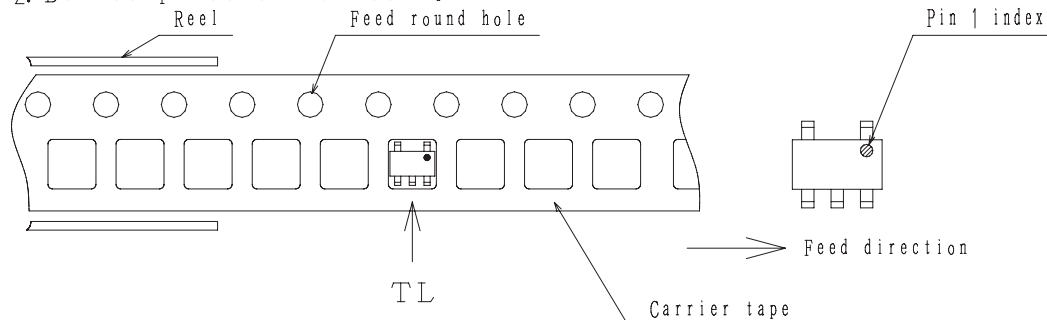
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)

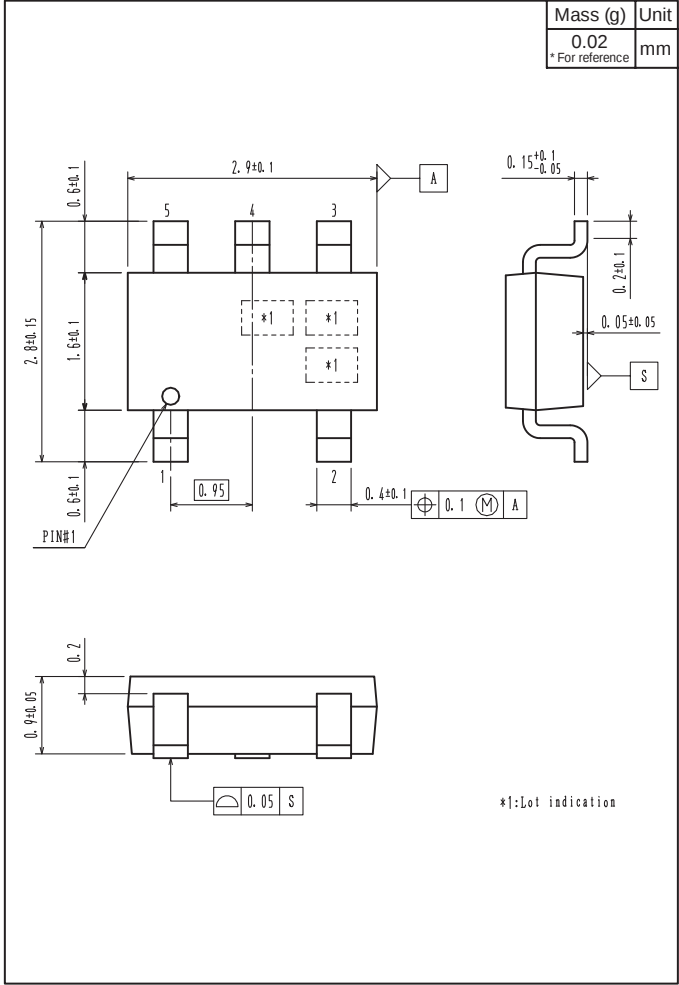


2-2. Device placement direction

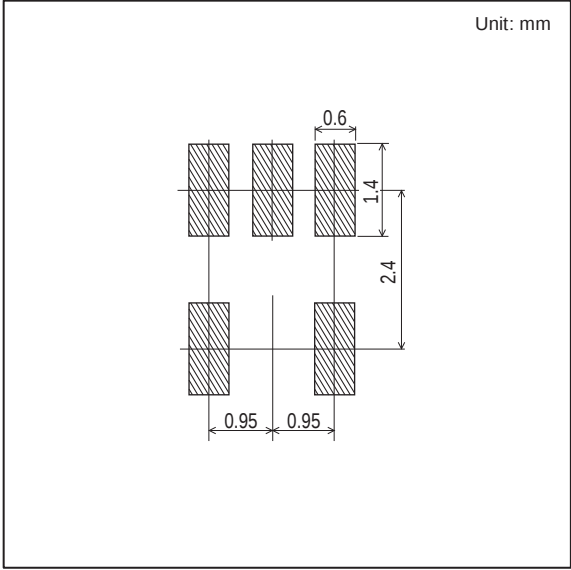


Those with pin 1 index on the feed hole side.....TL

Outline Drawing
CPH5520-TL-E



Land Pattern Example



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